

Advance data

Insulated Gate Bi-Polar Transistor

Type T1290BF65A

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	6500	V
V_{CES}	Collector – emitter voltage (T_j 25°C)	6500	V
V_{CES}	Collector – emitter voltage (T_j -40°C)	6000	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	3600	V
V_{GES}	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
I_C	DC collector current, IGBT	1290	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	2580	A
$I_{F(DC)}$	Continuous DC forward current, Diode	1290	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	2580	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	10.9	kA
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	12	kA
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	15.2	KW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	4500	A/ μs
T_j	Operating temperature range.	-40 to +125	°C
T_{stg}	Storage temperature range.	-40 to +125	°C

Notes: -

- 1) Unless otherwise indicated $T_j = 125^\circ C$.
- 2) $T_{sink} = 25^\circ C$, double side cooled.
- 3) Maximum commutation loop inductance 230nH.
- 4) Half-sinewave, 125°C T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _{CE(sat)}	Collector – emitter saturation voltage	-	3.6	4.0	I _C = 1290A, V _{GE} = 15V, T _j = 25°C	V
		-	4.8	5.2	I _C = 1290A, V _{GE} = 15V	V
V _{T0}	Threshold voltage	-		2.48	Current range: 430A – 1290A	V
r _T	Slope resistance	-		2.11		mΩ
V _{GE(TH)}	Gate threshold voltage	-	5.4	-	V _{CE} = V _{GE} , I _C = 800mA	V
I _{CES}	Collector – emitter cut-off current	-	12	45	V _{CE} = V _{CES} , V _{GE} = 0V	mA
I _{GES}	Gate leakage current	-40	-	+40	V _{GE} = ±20V	µA
C _{ies}	Input capacitance	-	225	-	V _{CE} = 10V, V _{GE} = 0V, f = 100kHz, T _j =25°C	nF
t _{d(on)}	Turn-on delay time	-	1.9	-	I _C = 1290A, V _{CE} = 3600V, di/dt = 3500A/µs V _{GE} = ±15V, L _S = 230nH R _{g(ON)} = 2.4Ω, R _{g(OFF)} = 7.5Ω, C _{GE} = 100nF Integral diode used as freewheel diode (Note 3)	µs
t _{r(V)}	Rise time	-	2.8	-		µs
Q _{g(on)}	Turn-on gate charge	-	7.5	-		µC
E _{on}	Turn-on energy	-	9	-		J
t _{d(off)}	Turn-off delay time	-	4.2	-		µs
t _{f(l)}	Fall time	-	2.2	-		µs
Q _{g(off)}	Turn-off gate charge	-	8	-		µC
E _{off}	Turn-off energy	-	7.3	-		J
I _{SC}	Short circuit current	-	7000	-		V _{GE} = +15V, V _{CC} = 3600V, V _{CEmax} ≤ V _{CES} , t _p ≤ 10µs

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _F	Forward voltage	-	3.2	3.6	I _F = 1290A, T _j = 25°C	V
		-	3.6	4.0	I _F = 1290A	V
V _{To}	Threshold voltage	-	-	1.56	Current range 430A – 1290A	V
r _T	Slope resistance	-	-	1.58		mΩ
I _{rm}	Peak reverse recovery current	-	1400	-	V _i = 3600V, I _F = 1290A, V _{GE} = -15V, di/dt = 3500A/µs	A
Q _{rr}	Recovered charge	-	1900	-		µC
t _{rr}	Reverse recovery time, 50% chord	-	1.1	-		µs
E _r	Reverse recovery energy	-	2.8	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R _{thJK}	Thermal resistance junction to sink, IGBT	-	-	6.56	Double side cooled	K/kW
		-	-	9.9	Collector side cooled	K/kW
		-	-	19.5	Emitter side cooled	K/kW
R _{thJK}	Thermal resistance junction to sink, Diode	-	-	12.2	Double side cooled	K/kW
		-	-	17.6	Cathode side cooled	K/kW
		-	-	39.3	Anode side cooled	K/kW
F	Mounting force	55	-	75	Note 2	kN
W _t	Weight	-	3.2	-		g

Notes:-

- 1) Unless otherwise indicated T_j = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

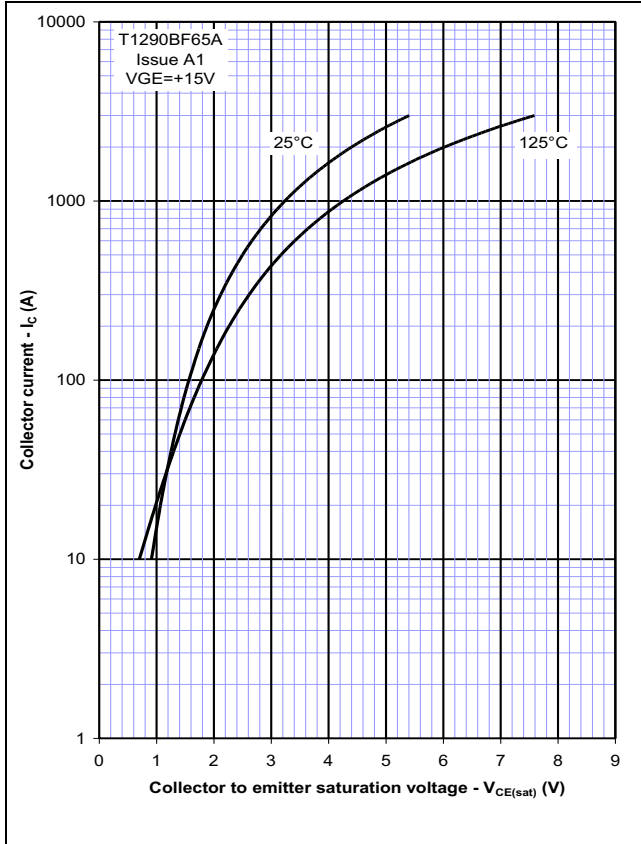


Figure 2 – Typical output characteristic

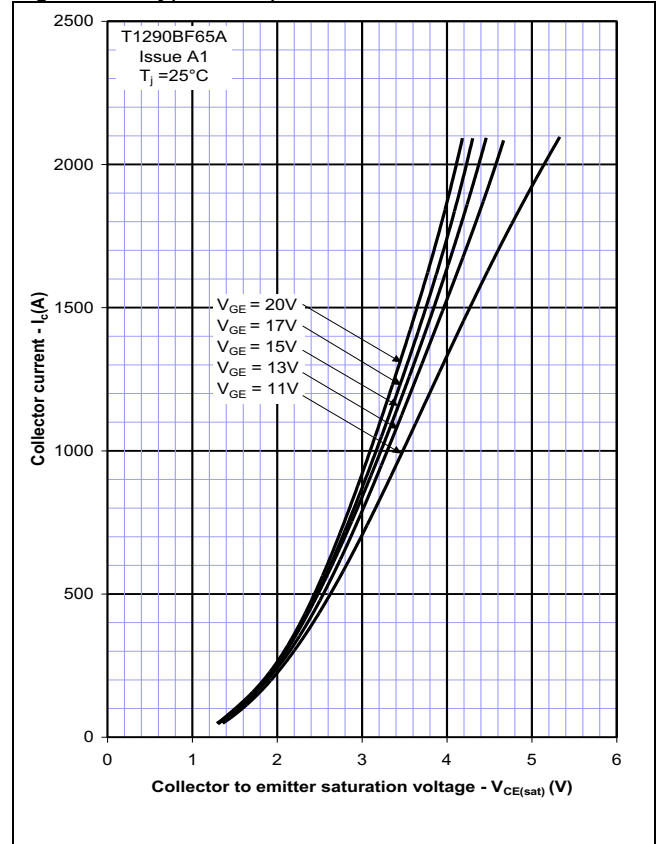


Figure 3 – Typical output characteristic

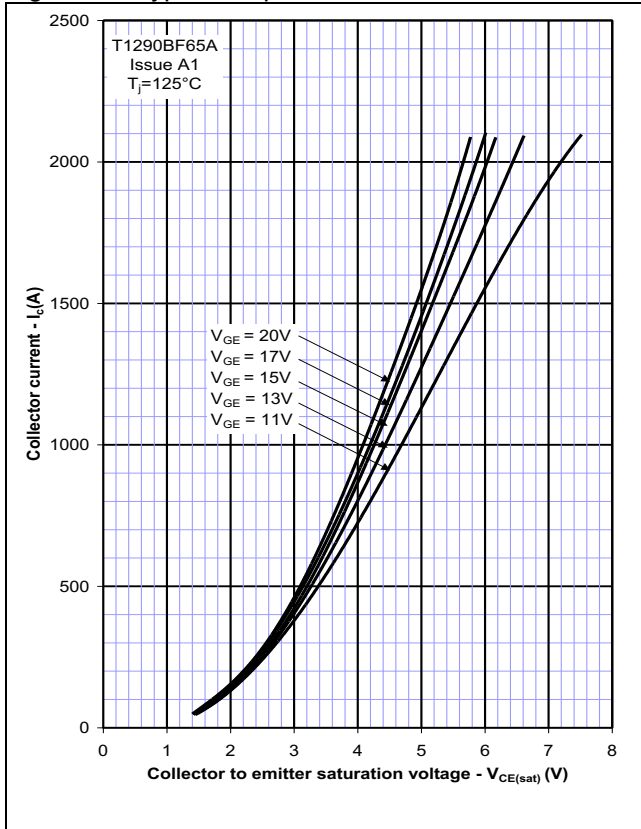


Figure 4 – Safe operating area (IGBT)

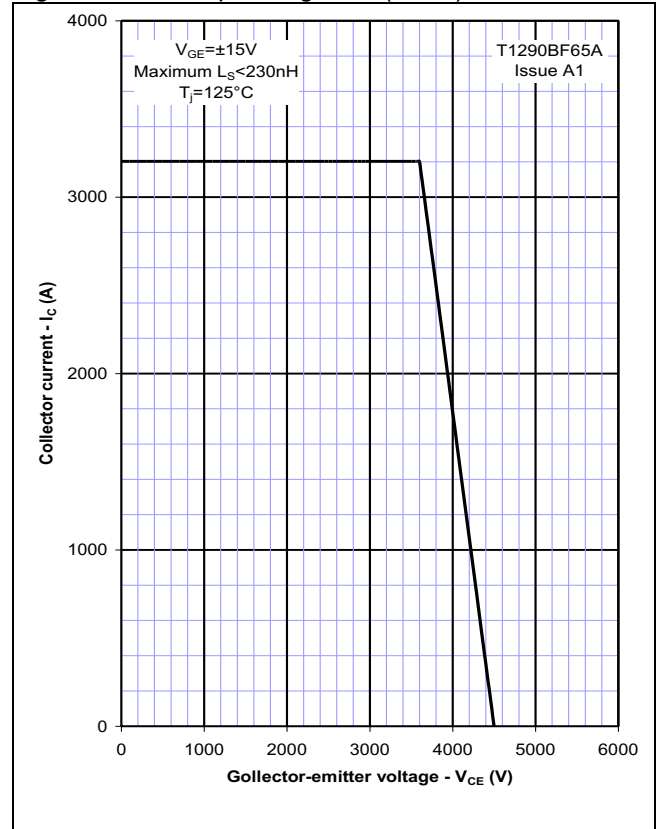


Figure 5 – Typical diode forward characteristics

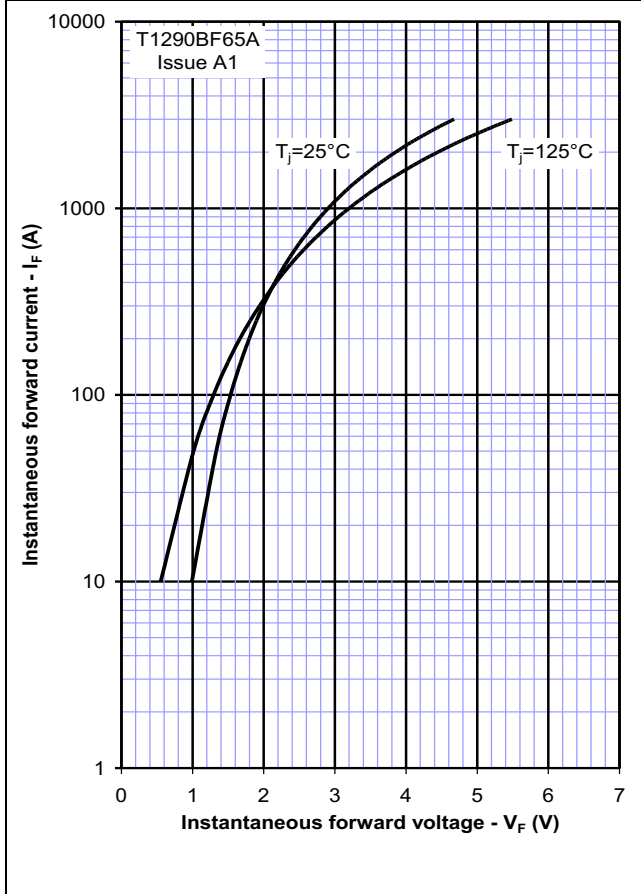


Figure 6 – Safe operating area (Diode)



Figure 7 – Transient thermal impedance (IGBT)

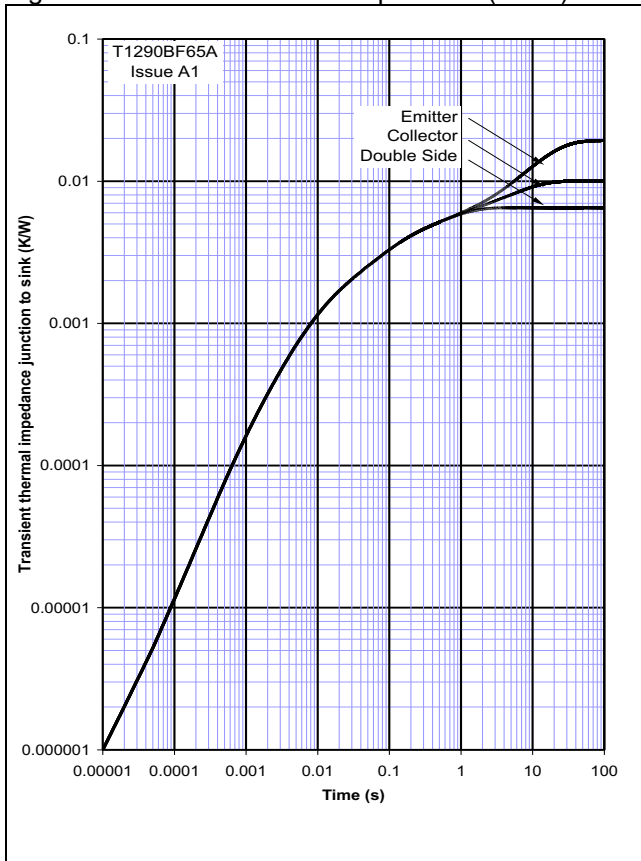
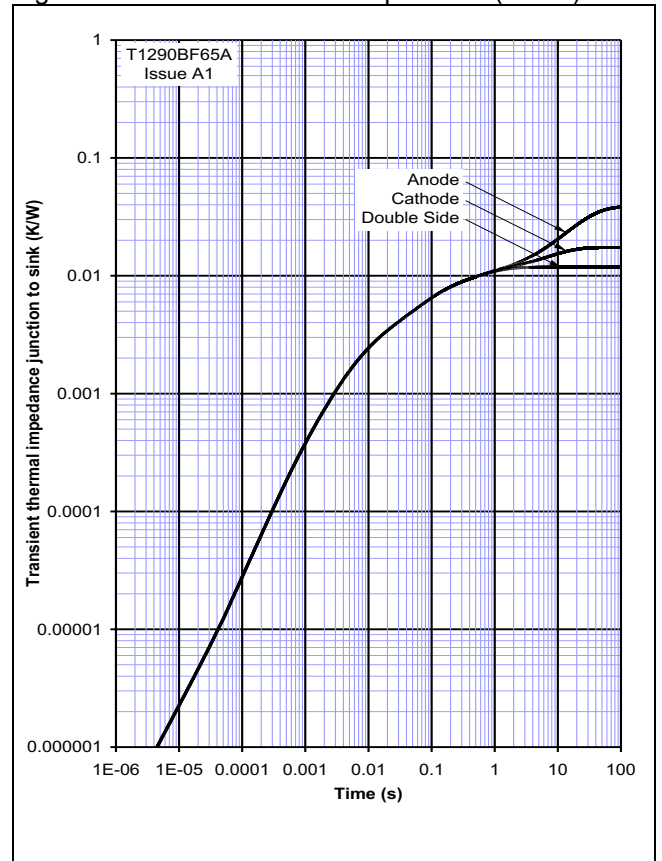
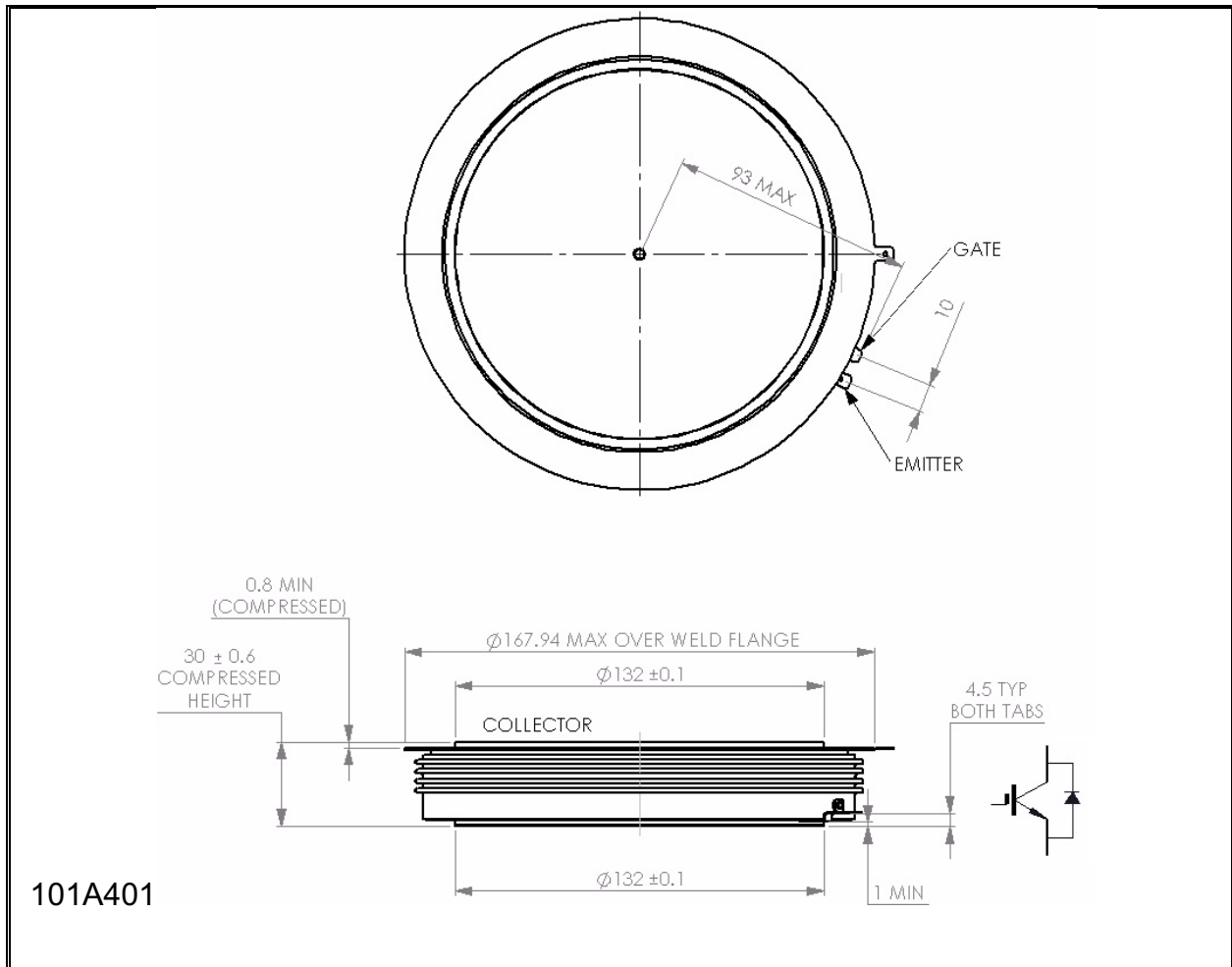


Figure 8 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

T1290	BF	65	A
Fixed type Code	Fixed Outline Code	Voltage Grade V _{CES} /100 65	Fixed format code

Typical order code: T1290BF65A (V_{CES} = 6500V)

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